

Power Factor Correction Controller

FAN7527B

Description

The FAN7527B provides simple and high-performance active Power Factor Correction (PFC). The FAN7527B is optimized for electronic ballasts and low-power, high-density power supplies that require minimum board size, reduced external components, and low power dissipation. Because the R/C filter is included in the current-sense block, an external R/C filter is not necessary. Special circuitry prevents no-load runaway conditions. Regardless of the supply voltage, the output drive clamping circuit limits the overshoot of the power MOSFET gate drive, which improves system reliability.

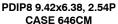
Features

- Internal Startup Timer
- Internal R/C Filter Eliminates the Need for External R/C Filter
- Precise Adjustable Output Over-Voltage Protection
- Zero Current Detector
- One Quadrant Multiplier
- Trimmed 1.5% Internal Band Gap Reference
- Under-Voltage Lockout with 3 V of Hysteresis
- Totem-Pole Output with High-State Clamp
- Low Startup and Operating Current
- 8-Pin SOP or 8-Pin DIP
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Electronic Ballast
- SMPS

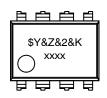




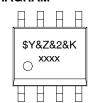


SOIC8 CASE 751EB

MARKING DIAGRAM



\$Y



= **onsemi** Logo

&Z = Assembly Plant Code
&2 = 2-Digit Date Code
&K = Lot Run Traceability Code

&K = Lot Run Traceability C xxxx = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping [†]
FAN7527BN	PDIP8 (Pb-Free)	3000 / Tube
FAN7527BMX	SOIC8 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NOTE: Operating Temperature Range of both devices is -25 to +125°C

BLOCK DIAGRAM

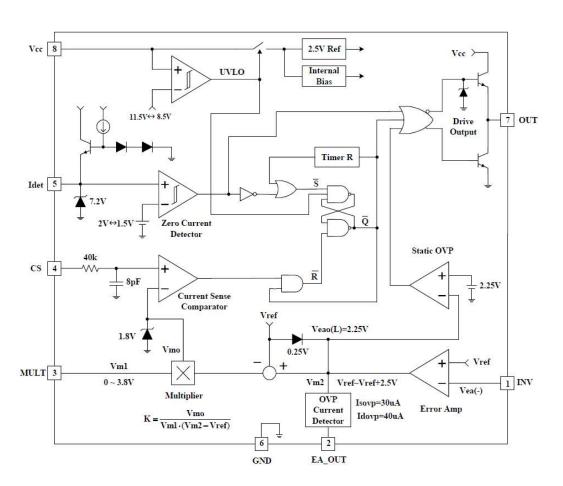


Figure 1. Block Diagram

PIN CONFIGURATION

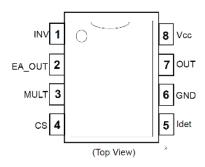


Figure 2. Pin Configuration

PIN DEFINITIONS

Pin #	Name	Description
1	INV	Inverting input of the error amplifier. The output of the boost converter should be resistively divided to 2.5 V and connected to this pin.
2	EA_OUT	Output of the error amplifier. Feedback compensation network is placed between this pin and the INV pin.
3	MULT	Input to the multiplier stage. The full-wave rectified AC voltage is divided to less than 2 V and is connected to this pin.
4	CS	Input of the PWM comparator. The MOSFET current is sensed by a resistor and the resulting voltage is applied to this pin. An internal R/C filter is included to reject high-frequency noise
5	ldet	Zero Current Detection (ZCD) input
6	GND	Ground
7	OUT	Gate driver output. Push-pull output stage is able to drive the power MOSFET with a peak current of 500 mA
8	V _{CC}	Supply voltage of driver and control circuits

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter			Max.	Unit
Vcc	Supply Voltage			30	V
Iон, Iol	Peak Drive Output Current			±500	mA
ICLAMP	Driver Output Clamping Diodes V _O > V _{CC} or V	V _O < -0.3 V		±10	mA
IDET	Detector Clamping Diodes	Detector Clamping Diodes		±10	mA
VIN	Error Amplifier Multiplier and Comparator Input Voltages		-0.3	6.0	V
TJ	Operation Junction Temperature			+150	°C
Topr	Operating Temperature Range		-25	+125	°C
Tstg	Storage Temperature Range		-65	+150	°C
Б	Power Dissipation	SOIC8		0.8	W
P_{D}		PDIP8		1.1	W
ΘЈА	Thermal Resistance Junction-Ambient	SOIC8		150	°C/W
OJA		PDIP8		110	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

TEMPERATURE CHARACTERISTICS

 $(-25^{\circ}C \leq T_A \leq 125^{\circ}C)$

Symbol	Parameter	Min.	Тур.	Max.	Unit
ΔV REF	Temperature Stability Reference Voltage (V _{REF})		20		mV
ΔΚ/ΔΤ	Temperature Stability for Multiplier Gain (K)		-0.2		% / °C

ELECTRICAL CHARACTERISTICS $(V_{CC} = 14 \text{ V, } -25^{\circ}\text{C} \leq T_{A} \leq 125^{\circ}\text{C}, \text{ unless otherwise stated.})$

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
JNDER-VOL	TAGE LOCKOUT			=	_	
Vth(st)	Start Threshold Voltage	V _{CC} Increasing	10.5	11.5	12.5	V
HY(st)	UVLO Hysteresis		2	3	4	V
SUPPLY CUR	RENT SECTION					
lsт	Startup Supply Current	$V_{CC} = V_{th(st)} - 0.2 \text{ V}$	10	60	100	μΑ
Icc	Operating Supply Current	Output Not Switching		3	6	mA
ICC(OVP)	Operating Current at OVP	V _{INV} = 3 V		1.7	4.0	mA
IDCC	Dynamic Operating Supply Current	50 kHz, C _I = 1 nF		4	8	mA
RROR AMP	LIFIER SECTION					
VREF	Voltage Feedback Input Threshold	I _{REF} = 0 mA, T _A = 25°C	2.465	2.500	2.535	V
		$25^{\circ}C \le T_{A} \le 125^{\circ}C$	2.440	2.500	2.560	
ΔV FEF1	Line Regulation	14 V ≤ V _{CC} ≤ 25 V		0.1	10.0	mV
ΔVFEF3	Temperature Stability of V _{REF} (Note 1)	$-25^{\circ}\text{C} \le \text{T}_{\text{A}} \le 125^{\circ}\text{C}$		20		mV
Ib(ea)	Input Bias Current		-0.5		0.5	μΑ
ISOURCE	Output Source Current	V _{M2} = 4 V	-2	-4		mA
Isink	Output Sink Current	V _{M2} = 4 V	2	4		mA
VEAO(H)	Output Upper Clamp Voltage (Note 1)	I _{SOURCE} = 0.1 mA		6		V
VEAO(L)	Output Lower Clamp Voltage (Note 1)	I _{SINK} = 0.1 mA		2.25		V
G _V	Large Signal Open-Loop Gain (Note 1)		60	80		dB
PSRR	Power Supply Rejection Ratio (Note 1)	14 V ≤ V _{CC} ≤ 25 V	60	80		dB
GBW	Unity Gain Bandwidth (Note 1)			1		MHz
SR	Slew Rate (Note 1)			0.6		V/μs
IULTIPLIER	SECTION		•	•	•	•
lb(m)	Input Bias Current (Pin 3)		-0.5		0.5	μА
ΔV_{M1}	M1 Input Voltage Range (Pin 3)				3.8	V
ΔV_{M2}	M2 Input Voltage Range (Pin 2)		VREF		V _{REF} +2.5	V
K	Multiplier Gain (Note 1)	V _{M1} = 1 V, V _{M2} = 3.5 V	0.36	0.44	0.52	1 / V
Vomax(m)	Maximum Multiplier Output Voltage	V _{INV} = 0 V, V _{M1} = 4 V	1.65	1.80	1.95	V
ΔΚ/ΔΤ	Temperature Stability of K (Note 1)	$-25^{\circ}C \le T_A \le 125^{\circ}C$		-0.2		%/°C
CURRENT SE	ENSE SECTION					
VIO(CS)	Input Offset Voltage (Note 1)	V _{M1} = 0 V, V _{M2} = 2.2 V	-10	3	10	mV
lb(CS)	Input Bias Current	0 V ≤ V _{CS} ≤ 1.7 V	-1.0	-0.1	1.0	μΑ
tD(CS)	Current Sense Delay to Output (Note 1)			200	500	ns
ERO CURRI	ENT DETECT SECTION		-			
VTH(DET)	Input Voltage Threshold	V _{DET} Increasing	1.7	2.0	2.3	V
HY(DET)	Detect Hysteresis		0.2	0.5	0.8	V
VCLAMP(I)	Input Low Clamp Voltage	I _{DET} = -100 μA	0.45	0.75	1.00	V
VCLAMP(H)	Input High Clamp Voltage	I _{DET} = 3 mA	6.5	7.2	7.9	V

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{CC} = 14 \text{ V}, -25^{\circ}\text{C} \le T_{A} \le 125^{\circ}\text{C}, \text{ unless otherwise stated.})$

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
ZERO CURRENT DETECT SECTION							
lb(DET)	Input Bias Current	1 V ≤ V _{DET} ≤ 5 V	-1.0	-0.1	1.0	μΑ	
ICLAMP(D)	Input High/Low Clamp Diode Current (Note 1)				±3	mA	
OUTPUT SEC	CTION						
Vон	Output Voltage High	I _O = -10 mA	10.5	11.0		٧	
Vol	Output Voltage Low	I _O = 10 mA		0.8	1.0	٧	
t _R	Rising Time (Note 1)	C _L = 1 nF		130	200	ns	
t _F	Falling Time (Note 1)	C _L = 1 nF		50	120	ns	
VOMAX(O)	Maximum Output Voltage	V_{CC} = 20 V, I_{O} = 100 μ A	12	14	16	V	
Vomin(o)	Output Voltage with UVLO Activated	$V_{CC} = 5 \text{ V}, I_{O} = 100 \mu\text{A}$			1	V	
RESTART TI	RESTART TIMER SECTION						
tD(RST)	Restart Time Delay	$V_{M1} = 1 \text{ V}, V_{M2} = 3.5 \text{ V}$		150		μs	
OVER-VOLT	OVER-VOLTAGE PROTECTION SECTION						
Isovp	Soft OVP Detecting Current		25	30	35	μΑ	
IDOVP	Dynamic OVP Detecting Current		35	40	45	μΑ	
Vovp	Static OVP Threshold Voltage	V _{INV} = 2.7 V	2.10	2.25	2.40	V	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. These parameters, although guaranteed, are not 100% tested in production.

Multiplier Gain:

$$\mathsf{K} = \frac{\mathsf{Pin4_Threshold}}{\mathsf{V_{M1}} \times \left(\mathsf{V_{M2}} - \mathsf{V_{REF}}\right)}$$

where $V_{M1} = V_{PIN3}$, $V_{M2} = V_{PIN2}$

TYPICAL PERFORMANCE CHARACTERISTICS

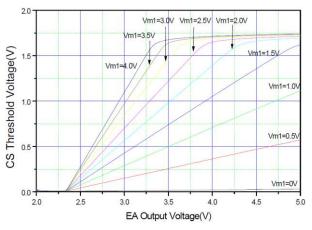


Figure 3. Error Amplifier Output Voltage vs. Current Sensing Threshold

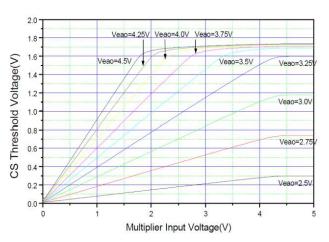


Figure 4. Multiplier Input Voltage vs. Current Sensing Threshold

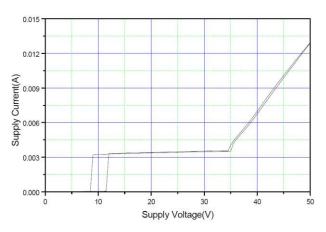


Figure 5. Supply Current vs. Supply Voltage

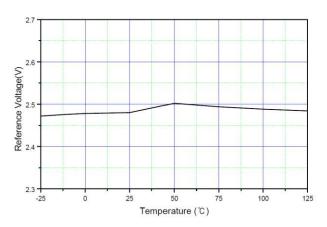


Figure 6. Reference Voltage vs. Temperature

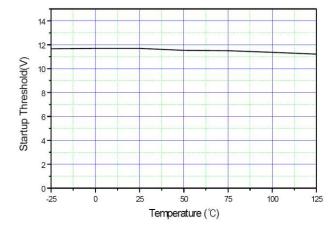


Figure 7. Startup Threshold vs. Temperature

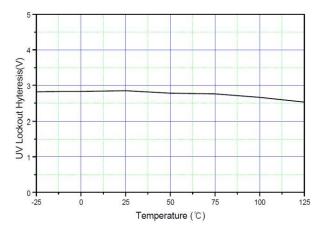


Figure 8. UVLO Hysteresis vs. Temperature

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

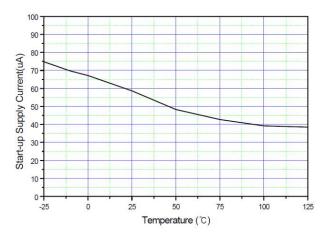


Figure 9. Startup Supply Current vs. Temperature

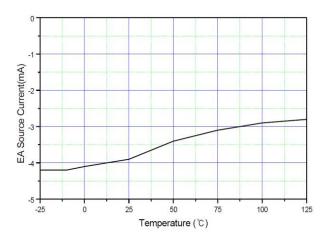


Figure 10. Error Amplifier Source Current

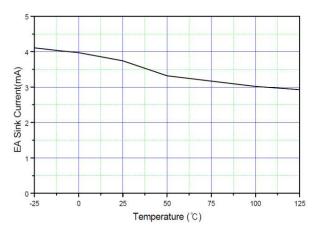


Figure 11. Error Amplifier Sink Current vs. Temperature

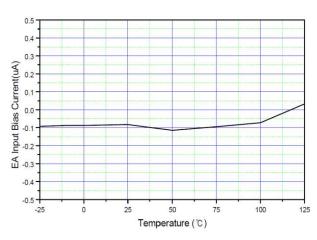


Figure 12. Error Amplifier Input Bias Current vs. Temperature

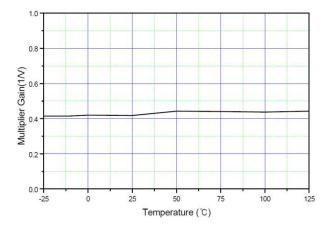


Figure 13. Multiplier Gain vs. Temperature

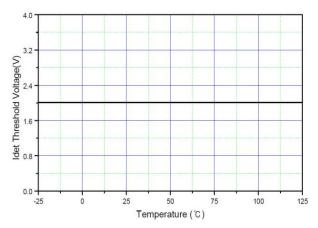


Figure 14. I_{DET} Threshold Voltage vs. Temperature

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

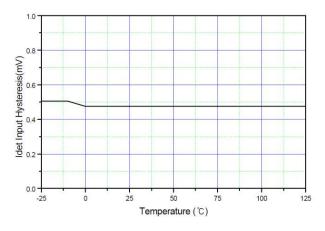
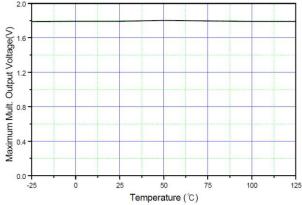


Figure 15. IDET Input Hysteresis vs. Temperature

Figure 16. Restart Time vs. Temperature





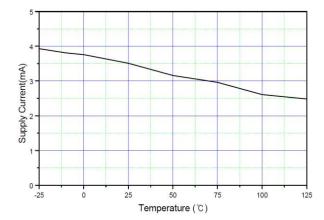
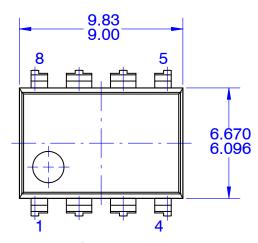


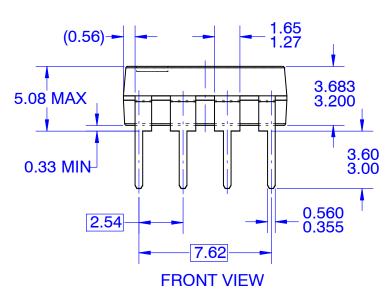
Figure 18. Supply Current vs. Temperature

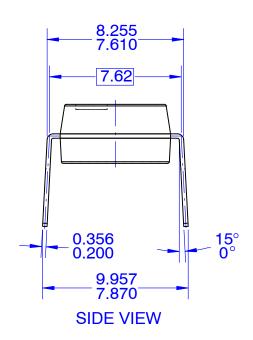
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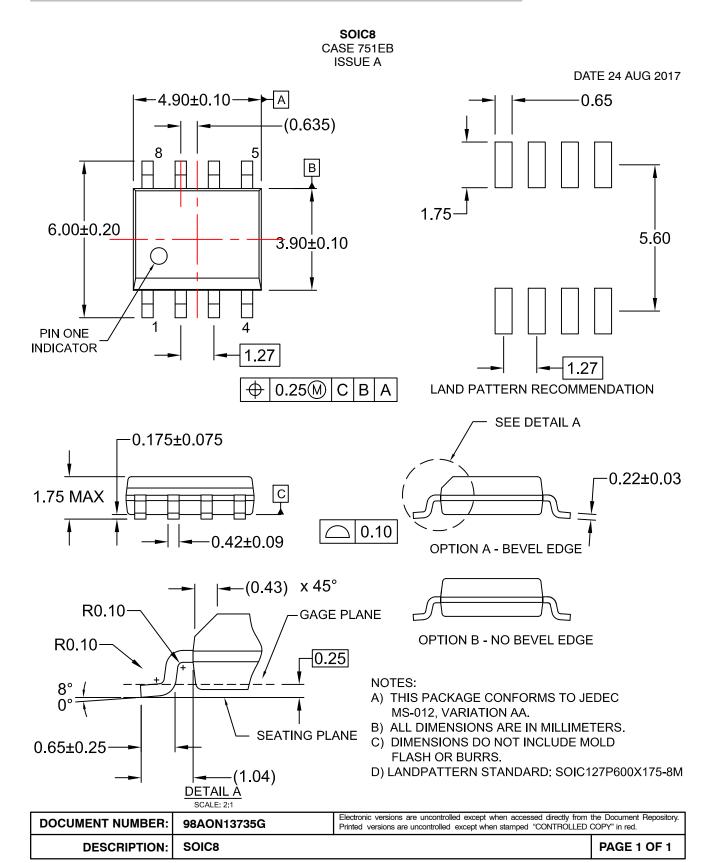


NOTES:

- A. CONFORMS TO JEDEC MS-001, VARIATION BA B. ALL DIMENSIONS ARE IN MILLIMETERS C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS D. DIMENSIONS AND TOLERANCES PER ASME Y14.5M-2009

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